

DOCKET NO. IB-1330D

Express Mailing Label No. EF333129215US

IN THE SPECIFICATION:

Page 1, line 4 (after the title), please add the following:

"CROSS-REFERENCE TO RELATED APPLICATION"

A
9/27/03
09/349,833 filed July 8, 1999, as a continuation of U.S. Patent Application Serial No. 09/349,833 filed Nov. 23, 1997, now U.S. Patent 5,990,479 issued November 23, 1999.
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now U.S. Patent 6,423,551 which is

[Please replace the paragraph beginning at page 9, line 1, with the following rewritten paragraph:

A2
--Formation of nanometer crystals of Group III-V semiconductors is described in copending and commonly assigned Alivisatos et al. U.S. Patent 5,751,018; Alivisatos et al. U.S. Patent 5,505,928; and Alivisatos et al. U.S. Patent 5,262,357, which also describes the formation of Group II-VI semiconductor nanocrystals, and which is also assigned to the assignee of this invention. Also described therein is the control of the size of the semiconductor nanocrystals during formation using crystal growth terminators. The teachings of Alivisatos et al. U.S. Patent 5,751,018 and Alivisatos et al. U.S. Patent 5,262,357 are each hereby specifically incorporated by reference.--